

DATA SHEET

LFE15600X

NPN microwave power transistor

Product specification
Supersedes data of January 1994

1997 Feb 19

NPN microwave power transistor

LFE15600X

FEATURES

- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Gold metallization realizes very good stability of the characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input and output prematching ensures good stability and allows an easier design of wideband circuits.

APPLICATIONS

Common emitter, class AB amplifiers in CW conditions for professional applications between 1.5 GHz and 1.7 GHz.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT448A glued cap metal ceramic flange package, with emitter connected to flange.

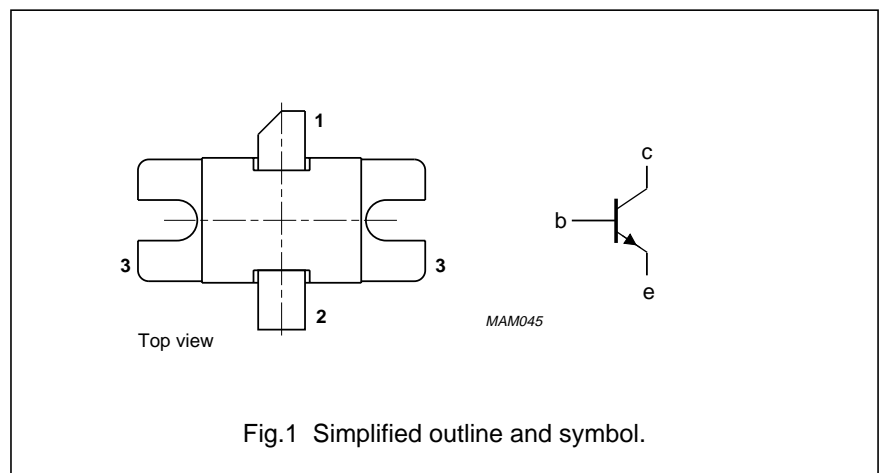
QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^\circ\text{C}$ in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V _{CE} (V)	I _{CQ} (A)	P _{L1} (W)	G _{po} (dB)	η _c (%)	Z _i /Z _L (Ω)
Class AB (CW)	1.5	24	0.2	≥55	≥8	typ.50	see Figs 7 and 8

PINNING - SOT448A

PIN	DESCRIPTION
1	collector
2	base
3	emitter connected to flange



WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	45	V
V _{CER}	collector-emitter voltage	R _{BE} = 56 Ω	–	30	V
V _{CEO}	collector-emitter voltage	open base	–	22	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	DC collector current		–	12	A
P _i	input power	f = 1.5 GHz; V _{CE} = 24 V; class AB	–	20	W
P _{tot}	total power dissipation	T _{mb} = 75 °C	–	80	W
T _{stg}	storage temperature		–65	+200	°C
T _j	junction temperature		–	200	°C
T _{sld}	soldering temperature	t ≤ 10 s; note 1	–	235	°C

Note

- Up to 0.2 mm from ceramic.

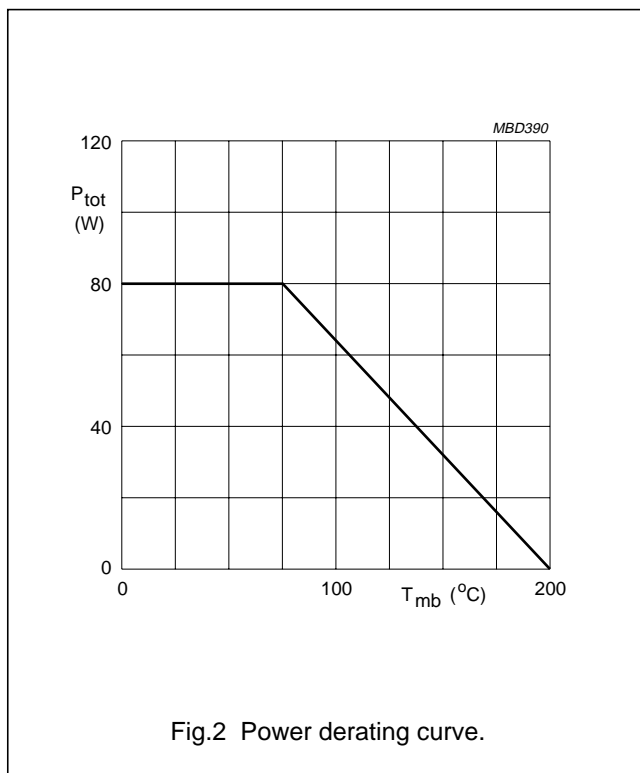


Fig.2 Power derating curve.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 100\text{ °C}$	1.2	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	note 1	0.2	K/W

Note

- See "Mounting recommendations in the General part of handbook SC19a".

CHARACTERISTICS

$T_{mb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	6	mA
$V_{(BR)CER}$	collector-emitter breakdown voltage	$I_C = 30\text{ mA}; R_{BE} = 56\ \Omega$	30	–	V
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 30\text{ mA}$	45	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 30\text{ mA}$	3	–	V
h_{FE}	DC current gain	$I_C = 1\text{ A}; V_{CE} = 5\text{ V}$	15	100	

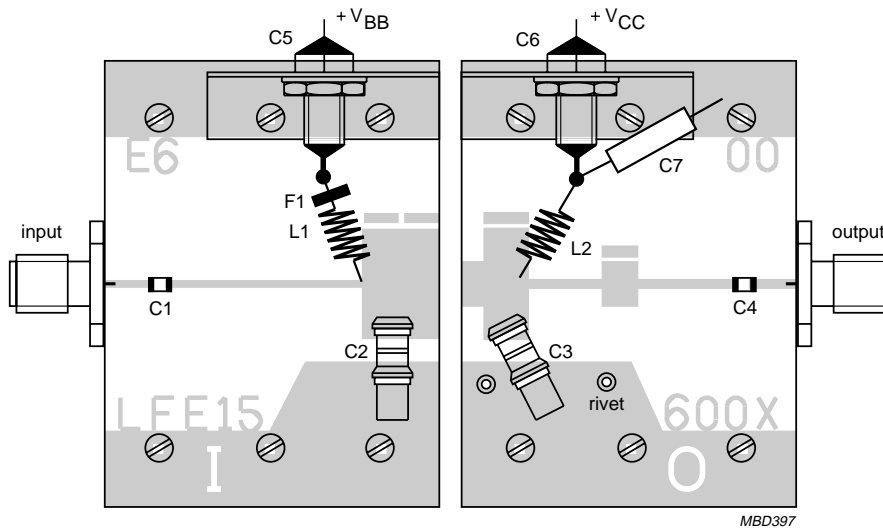
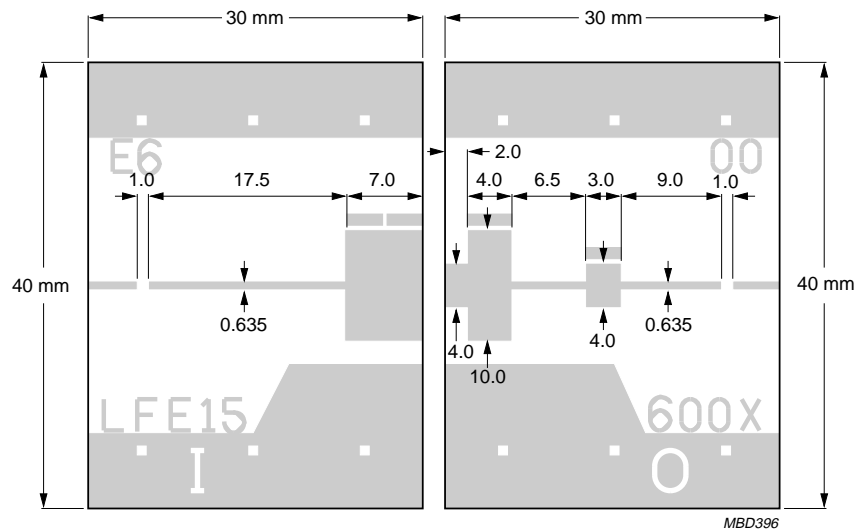
APPLICATION INFORMATION

Microwave performance up to $T_{mb} = 25\text{ °C}$ in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V_{CE} (V)	I_{CQ} (A)	P_{L1} (W)	G_{po} (dB)	η_c (%)	Z_i/Z_L (Ω)
Class AB (CW)	1.5	24	0.2	≥ 55 typ. 60	≥ 8 typ. 8.5	typ. 50	see Figs 7 and 8

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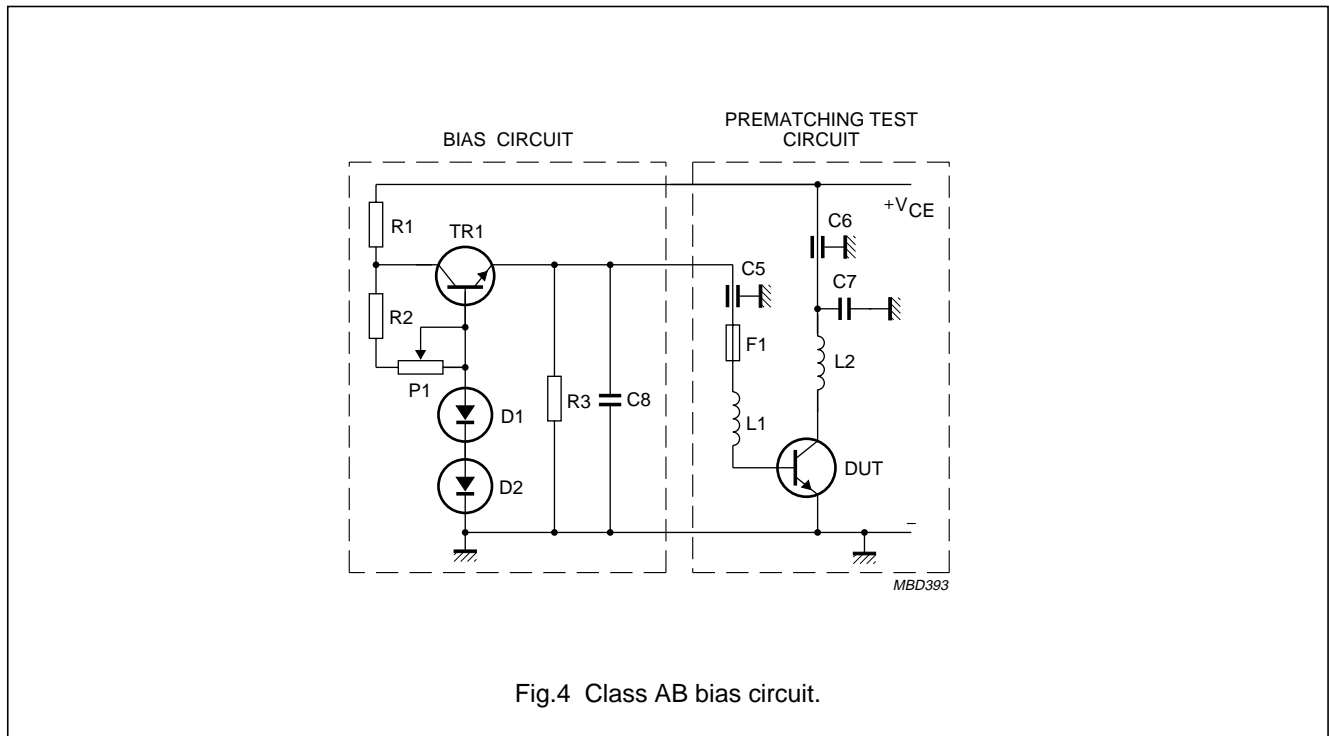


The test circuit is split into 2 independent halves, each being 30 × 40 mm in size.
 Dimensions in mm.
 Substrate: Epsilam 10.
 Thickness: 0.635 mm.
 Permittivity: $\epsilon_r = 10$.

Fig.3 Prematching test circuit board.

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List of components (see Figs 3 and 4)

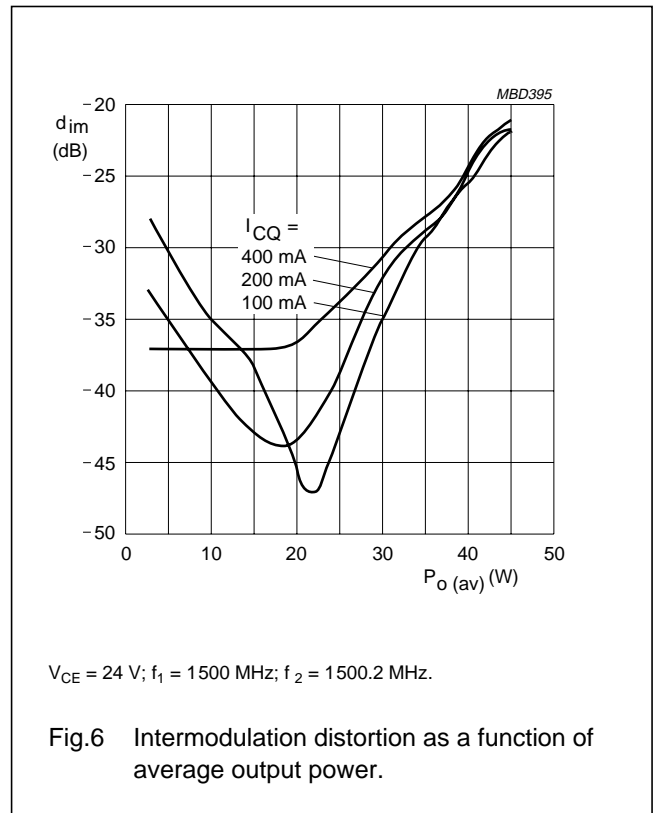
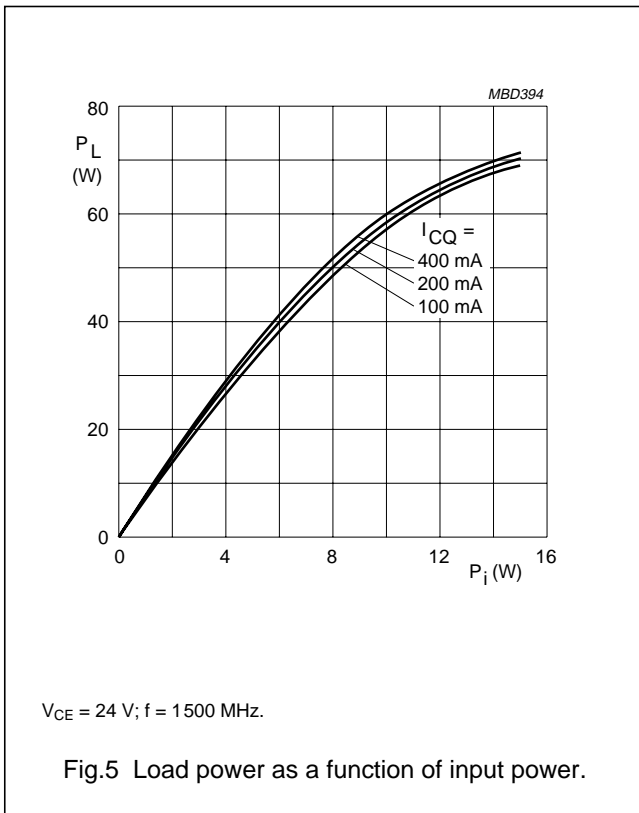
COMPONENT	DESCRIPTION	VALUE	TYPE NUMBERS
TR1	transistor		BDT91 or equivalent
C1, C4	DC blocking chip capacitor	100 pF	ATC 100A101kp
C2, C3	trimmer capacitor	0.5 to 5.0 pF	Tekelec 727-1
C5, C6	feedthrough bypass capacitor	1500 pF	Erie, ref. 1250-003
C7, C8	tantalum capacitor	10 μ F, 50 V	
D1	diode BY239 or equivalent; note 1		
D2	diode BY239 or equivalent; note 2		
L1	4 turns 0.5 mm copper wire; internal diameter = 2 mm		
L2	3 turns 0.5 mm copper wire; internal diameter = 2 mm		
P1	linear potentiometer	4.7 k Ω	
R1	resistor	100 Ω , 0.25 W	
R2	resistor	10 k Ω , 0.25 W	
R3	resistor	50 Ω , 0.25 W	
F1	ferrite bead		Philips tube 3.7 \times 1.2 \times 3.5 mm (3B)

Notes

1. In thermal contact with TR1.
2. In thermal contact with DUT.

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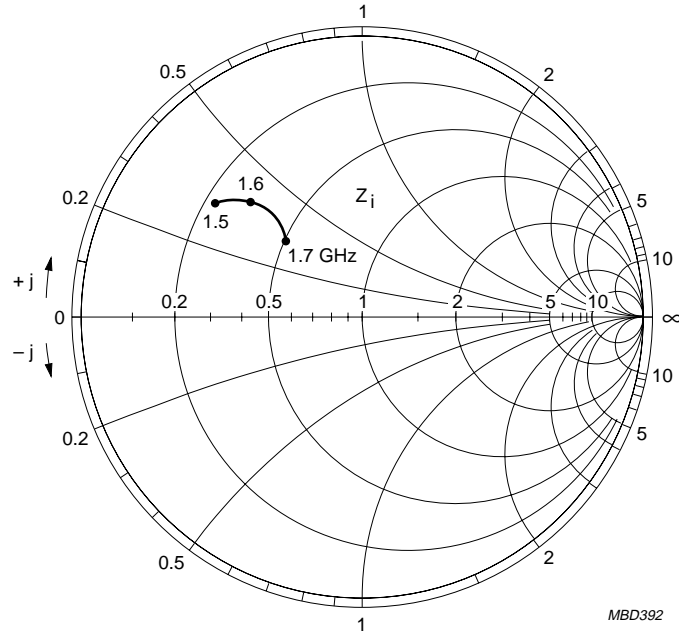
Input and optimum load impedances

$V_{CE} = 24\text{ V}; I_{CQ} = 0.2\text{ A}.$

f (GHz)	Z_i (Ω)	Z_L (Ω)
1.50	$2.4 + j3.4$	$2.4 - j1.8$
1.55	$3.0 + j3.6$	$2.3 - j1.7$
1.60	$3.5 + j3.8$	$2.2 - j1.6$
1.65	$4.2 + j3.8$	$2.1 - j1.5$
1.70	$4.8 + j2.5$	$1.8 - j1.5$

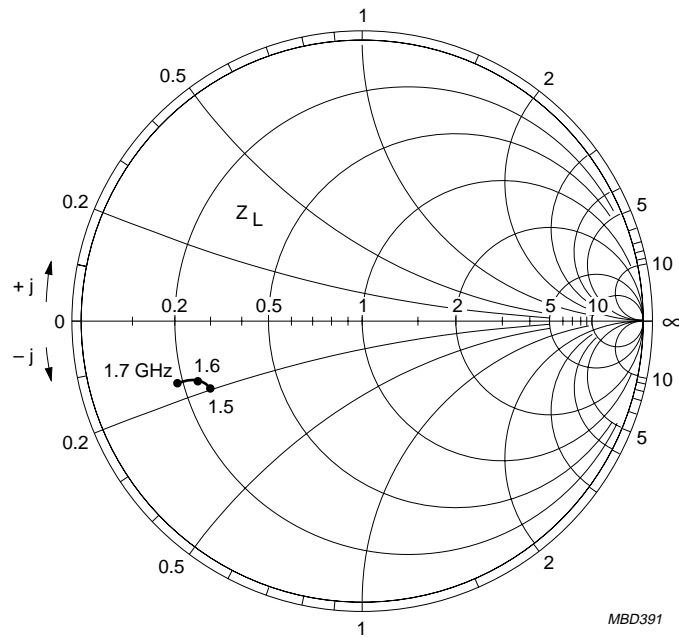
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$V_{CE} = 24 \text{ V}; Z_o = 10 \Omega; I_{CQ} = 0.2 \text{ A}.$

Fig.7 Input impedance as a function of frequency; typical values.



$V_{CE} = 24 \text{ V}; Z_o = 10 \Omega; I_{CQ} = 0.2 \text{ A}.$

Fig.8 Optimum load impedance as a function of frequency; typical values.

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DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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NOTES

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Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

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Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
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Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
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Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 1949

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580/xxx

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, TEL AVIV 61180,
Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
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Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

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Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
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Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
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Slovakia: see Austria

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
04552-903 São Paulo, SÃO PAULO - SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
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Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
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Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
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United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
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United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
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